



**MAIL STOP PCT**

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Docket No. 292759US0PCT

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

IN RE APPLICATION OF: Frederic MAZEN, et al.

SERIAL NO: 10/584,053

GAU:

FILED: June 22, 2006

EXAMINER:

FOR: METHOD FOR THE ORGANISED GROWTH OF NANOSTRUCTURES

**INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97**

COMMISSIONER FOR PATENTS  
ALEXANDRIA, VIRGINIA 22313

SIR:

Applicant(s) wish to disclose the following information.

**REFERENCES**

- ☒ The applicant(s) wish to make of record the references cited in the International Search Report and listed on the attached form PTO-1449. Copies of the listed references are attached, where required, as are either statements of relevancy or any readily available English translations of pertinent portions of any non-English language references.
- ☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

**RELATED CASES**

- ☐ Attached is a list of applicant's pending application(s), published application(s) or issued patent(s) which may be related to the present application. In accordance with the waiver of 37 CFR 1.98 dated September 21, 2004, copies of the cited pending applications are not provided. Cited published and/or issued patents, if any, are listed on the attached PTO form 1449.
- ☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

**CERTIFICATION**

- ☐ Each item of information contained in this information disclosure statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.
- ☐ No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

**DEPOSIT ACCOUNT**

- ☒ Please charge any additional fees for the papers being filed herewith and for which no check or credit card payment is enclosed herewith, or credit any overpayment to deposit account number 15-0030. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

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ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /J.M./



Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 292759US0PCT		SERIAL NO. 10/584,053		
LIST OF REFERENCES CITED BY APPLICANT				APPLICANT Frederic MAZEN, et al.				
				FILING DATE June 22, 2006		GROUP		
U.S. PATENT DOCUMENTS								
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE	
	AA	5 935 454	08/10/1999	TADA et al.				
	AB	4 908 226	03/13/1990	KUBENA et al.				
	AC	2003 0157744	08/21/2003	SCHLAF				
	AD	5 082 359	01/21/1992	KIRKPATRICK				
	AE							
	AF							
	AG							
	AH							
	AI							
	AJ							
	AK							
	AL							
	AM							
	AN							
FOREIGN PATENT DOCUMENTS								
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES NO			
	AO							
	AP							
	AQ							
	AR							
	AS							
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)								
	AT	KUBENA R. L. et al., "SELECTIVE AREA NUCLEATION FOR METAL CHEMICAL VAPOR DEPOSITION USING FOCUSED ION BEAMS", JOURNAL OF VACUUM SCIENCE AND TECHNOLOGY, Vol. B6 (6), pages1865-1868, XP 000133336, 1988						
	AU	GERLACH R., "FOCUSED ION BEAM METHODS OF NANOFABRICATION: ROOM AT THE BOTTOM", PROCEEDINGS OF SPIE, Vol. 4510, pages 96-106, XP 008035414, 2001						
	AV	SCHMUKI P. et al., "SELECTIVE ELECTRODEPOSITION OF MICROPATTERNS ON PREDEFINED SURFACE DEFECTS ON P-Si (100)", JOURNAL OF ELECTROCHEMICAL SOCIETY, Vol. 148, pages 177-182, 2001						
	AW	BARON T. et al., "SILICON QUANTUM DOT NUCLEATION ON Si3 N4, SiO2, AND SiOx Ny SUBSTRATES FOR NANOELECTRONIC DEVICES", JOURNAL OF CRYSTAL GROWTH, Vol. 209, pages 1004-1008, 2000						
	AX	BARON T. et al., "NUCLEATION CONTOL OF CVD GROWTH SILICON NANOCRYSTALS FOR QUANTUM DEVICES", MICROELECTRONIC ENGINEERING, Vol. 61-62, pages 511-515, 2002						
	AY							
	AZ					<input type="checkbox"/> Additional References sheet(s) attached		
Examiner				/Joseph Miller, Jr/		Date Considered 01/13/2009		
*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.								

ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /J.M./

U.S. PCT Application Serial No: 10/584,053

Filed: June 22, 2006

Frederic MAZEN, et al.

Docket No. 292759 US

#### STATEMENT OF RELEVANCY

- 1) References AA-AD & AT-AU have been cited in the International Search Report. A copy of these references is being submitted herewith.
- 2) References            have been cited in the corresponding            Search Report. A copy of these references is being submitted herewith.
- 3) References AV-AX are discussed in the specification. A copy of these references is being submitted herewith.
- 4) References            are additional prior art known to Applicant. A copy of these references is being submitted herewith.

ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /J.M./